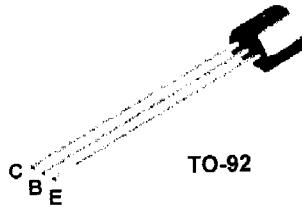


2N5770



NPN RF Transistor

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	4.5	V
I _C	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

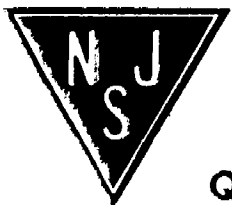
*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N5770	
P _D	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	125	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	357	°C/W



NJ Semi-Conductors reserves the right to change test conditions, parameters limits and package dimensions without notice information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

Electrical Characteristics

TA = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 3.0 \text{ mA}, I_B = 0$	15		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 1.0 \text{ }\mu\text{A}, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ }\mu\text{A}, I_C = 0$	4.5		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, I_E = 0$ $V_{CB} = 15 \text{ V}, I_E = 0, T_A = 150 \text{ }^\circ\text{C}$		10 1.0	nA μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_C = 0$ $V_{EB} = 2.0 \text{ V}, I_C = 0$		10 1.0	μA μA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_C = 3.0 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_C = 8.0 \text{ mA}$	20 50	200	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		1.0	V

SMALL SIGNAL CHARACTERISTICS

NF	Noise Figure	$I_C = 1.0 \text{ mA}, V_{CE} = 8.0 \text{ V},$ $f = 60 \text{ MHz}, R_g = 400 \text{ }\Omega$		6.0	dB
C_{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$	0.7	1.1	pF
C_{ib}	Input Capacitance	$V_{EB} = 0.5 \text{ V}$		2.0	pF
h_{fe}	Small-Signal Current Gain	$I_C = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $I_C = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	9.0 40	18 240	
$r_b C_c$	Collector-Base Time Constant	$I_E = 8.0 \text{ mA}, V_{CB} = 10 \text{ V},$ $f = 79.8 \text{ MHz}$	3.0	20	pS

FUNCTIONAL TEST

G_{pe}	Amplifier Power Gain	$I_C = 6.0 \text{ mA}, V_{CB} = 12 \text{ V},$ $f = 200 \text{ MHz}$	15		dB
P_O	Power Output	$V_{CC} = 15 \text{ V}, I_C = 8.0 \text{ mA},$	30		mW
η	Collector Efficiency	$f = 500 \text{ MHz}$	25		%

* Pulse Test: Pulse Width $\leq 300 \text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$